



pioneers in photolithography





# **DWL** 66<sup>+</sup>

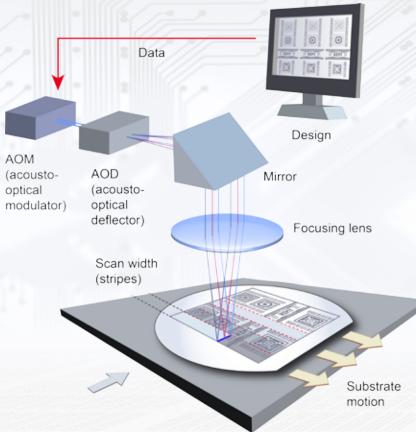
The Ultimate Lithography Research Tool

### DWL 66\* - the ultimate photolithography tool for Research & Development

The DWL 66<sup>+</sup> laser lithography system is a highly versatile, high-resolution pattern generator for low-volume mask making and direct writing. Its customer base includes over 250 leading universities, research facilities, and companies worldwide.

The system features powerful standard options such as the *High-Resolution Mode*, backside alignment (BSA), and the optical autofocus. In addition to high-resolution 2D patterns, the system also supports the creation of complex 3D





structures in thick photoresist with the help of the grayscale exposure mode. The DWL 66+ can be equipped with either a 405 nm laser for work with all broadband resists, or with a 375 nm UV laser that in addition allows the use of SU-8 and other i-line-resists. Advanced professional options like the *High-Accuracy Coordinate System* and an automatic loader are also available.

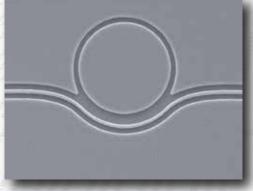
With a minimum structure size of 300 nm, the DWL 66+ provides the ultimate in high resolution, outperforming the most powerful optical lithography systems in the Research & Development market segment. The system's main application areas can be found in optical sciences, material research, micro-engineering and micro-electronics.

## The high-resolution mode

This is one of the six write modes that are available for the DWL 66<sup>+</sup>. The optimized optics and electronics setup of the *HiRes Write Mode* provide ultimate stability and resolution and enable exposures of structures with a minimum feature size of 300 nm.



Minimum feature size: 300 nm - or even less. The image shows the result of a high-resolution test exposure with a nominal linewidth of 250 nm!

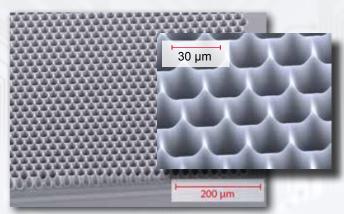


A channel waveguide coupled to a ring resonator. The waveguide is approximately 320 nm wide, the resonator diameter is 3 µm. The exposure laser wavelength was 405 nm. Design created with [1].

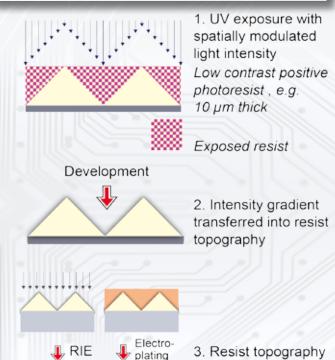
#### A choice of grayscale capabilities

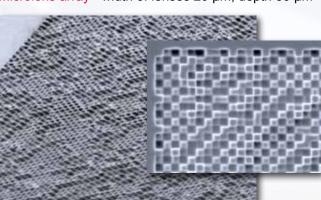
Grayscale lithography uses a low-contrast positive photoresist. The exposure intensity gradient transfers directly into exposure depth. The result after processing is a 3D topography on the microscale.

Whether basic, advanced or professional - the grayscale mode presents a powerful tool for the creation of *complex topographies* - for example for micro-optical components or MEMS.

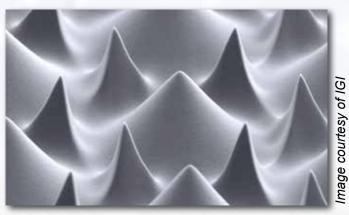


Microlens array - width of lenses 20 μm, depth 30 μm





DOE - resist AZ 4633, resist thickness 4  $\mu m$ , structure size 2  $\mu m$ 



transferred into substrate topography

Diffuser - resist AZ 4562, structure size  $< 5 \mu m$ 

## Advanced options and upgrades

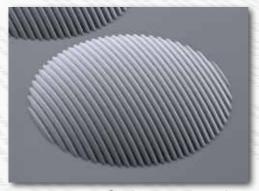
- Professional Grayscale Exposure Mode
   Allows the exposure of CAD files with up to
   1000 gray levels in order to create complex
   topographies for applications such as micro optics. Includes highly sophisticated software
   package.
- High-Accuracy Coordinate System
   Includes various technical measures to improve the thermal stability and position accuracy of the stage's coordinate system.

   Provides improved specifications for 2nd layer overlay accuracy.
- Automatic Loader

Handling of masks up to 7" and wafers up to 8". Optional second cassette station. Pre-aligner and wafer scanner available.

• Basic Freeform (BFF)

Exposures on non-planar substrates with features down to 3  $\mu$ m. Typical applications are microstructures on top of convex or concave lenses.



Grating on concave lens

Courtesy of Fraunhofer IOF

Write mode	HiRes	I	Ш	Ш	IV	V
Writing performance						
Minimum structure size [µm]	0.3	0.6	0.8	1	2	4
Minimum lines and spaces [half pitch, μm]	0.5	0.8	1	1.5	3	5
Address grid [nm]	5	10	25	50	100	200
Edge roughness [3σ, nm]	50	50	70	80	110	160
CD uniformity [3σ, nm]	60	70	80	130	180	250
Alignment measurement accuracy [3σ, nm]	100	100	150	250	400	800
2nd layer alignment over 100 x 100 mm² [3σ, nm]	500	500	500	500	800	1000
Max. write speed 405 nm laser [mm²/min]	3	13	40	150	600	2000
Max. write speed 375 nm laser [mm²/min]	2	10	30	110	-	-

S	ys	tem	tea	tur	es

Light source	Diode laser with 405 nm or 375 nm
Substrate sizes	Variable: 3 x 3 mm² to 9" x 9"   Customizable on request
Substrate thickness	0 to 12 mm
Maximum exposure area	200 x 200 mm <sup>2</sup>
Temperature controlled flow box	Temperature stability $\pm$ 0.1°, ISO 4 environment
Real-time autofocus	Optical autofocus or air-gauge autofocus
Autofocus compensation range	80 μm
Basic or Advanced Grayscale Mode	128 / 255 gray levels respectively
Vector mode	Enables the writing of stitching-free lines
Backside alignment (optional)	Allows to align exposures to structures on the backside of the substrate

#### Advanced options - performance upgrades

High-Accuracy Coordinate System	Includes golden plate calibration and climate monitoring: 2nd layer alignment down to 350 nm
Professional Grayscale Mode	1000 gray levels, professional data conversion software
Automatic loading system	Automatic loading unit, optional additional cassette station, optional pre-aligner and wafer scanner

#### System dimensions of standard version

Height × width × depth	1950 mm × 1300 mm × 1100 mm (lithography unit only)
Weight	1000 kg (lithography unit only)

#### Installation requirements

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Electrical	230 VAC ± 5 %, 50/60 Hz, 16 A
Compressed air	6 - 10 bar

**Please note:** Specifications depend on individual process conditions and may vary according to equipment configuration. Write speed depends on exposure area. Design and specifications are subject to change without prior notice.





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